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# Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China











# 40V 175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C (Note 10)
40V	$8.6 m\Omega @ V_{GS} = 10V$	45A

# **Description and Applications**

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

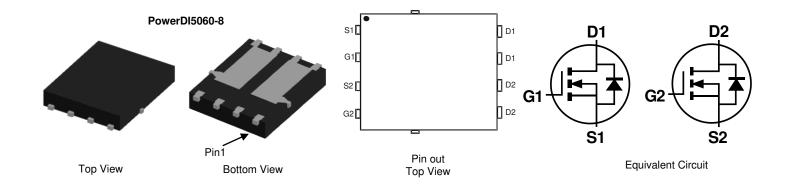
- Backlighting
- Power Management Functions
- DC-DC Converters

#### **Features and Benefits**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

#### **Mechanical Data**

- Case: PowerDI<sup>®</sup>5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208 (2)
- Weight: 0.097 grams (Approximate)



#### **Ordering Information** (Note 5)

Part Number	Case	Packaging
DMTH4007SPDQ-13	PowerDI5060-8	2.500/Tape & Reel

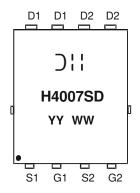
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Please refer to http://www.diodes.com/product\_compliance\_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Document number: DS38393 Rev. 1 - 2



### **Marking Information**



);; = Manufacturer's Marking H4007SD = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 15 = 2015) WW = Week (01 - 53)

# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V <sub>DSS</sub>	40	V		
Gate-Source Voltage	V <sub>GSS</sub>	±20	V		
Continuous Drain Current (Note 7)	T <sub>C</sub> = +25°C (Note 10)	I <sub>D</sub>	45	А	
	$T_{C} = +100^{\circ}C$		38.1		
Continuous Drain Current (Note 6)	I <sub>D</sub>	14.2 11.9	А		
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	90	A		
Maximum Continuous Body Diode Forward Current (Note 7)	Is	34	A		
Avalanche Current, L = 0.1mH	las	20	A		
Avalanche Energy, L = 0.1mH	E <sub>AS</sub>	20	mJ		

#### **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6) $T_A = +25^{\circ}C$		P <sub>D</sub>	2.6	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	57	°C/W	
Total Power Dissipation (Note 7) $T_C = +25^{\circ}C$		P <sub>D</sub>	37.5	W
Thermal Resistance, Junction to Case (Note 7)	$R_{ heta JC}$	4	°C/W	
Operating and Storage Temperature Range	$T_{J_1}T_{STG}$	-55 to +175	°C	

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz. copper, with thermal bias to bottom layer 1inch square copper plate.

7. Thermal resistance from junction to soldering point (on the exposed drain pad).

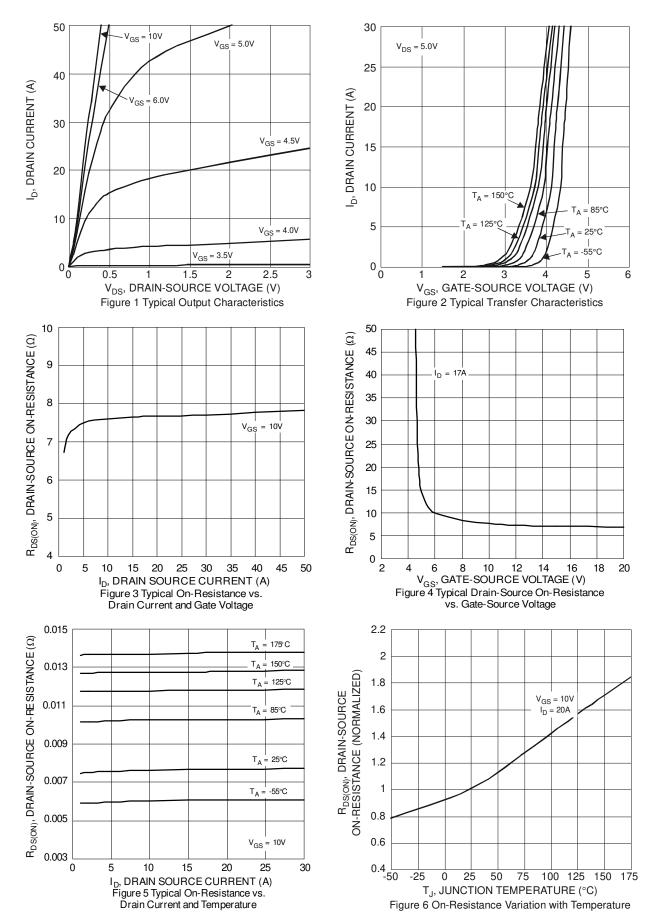


### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

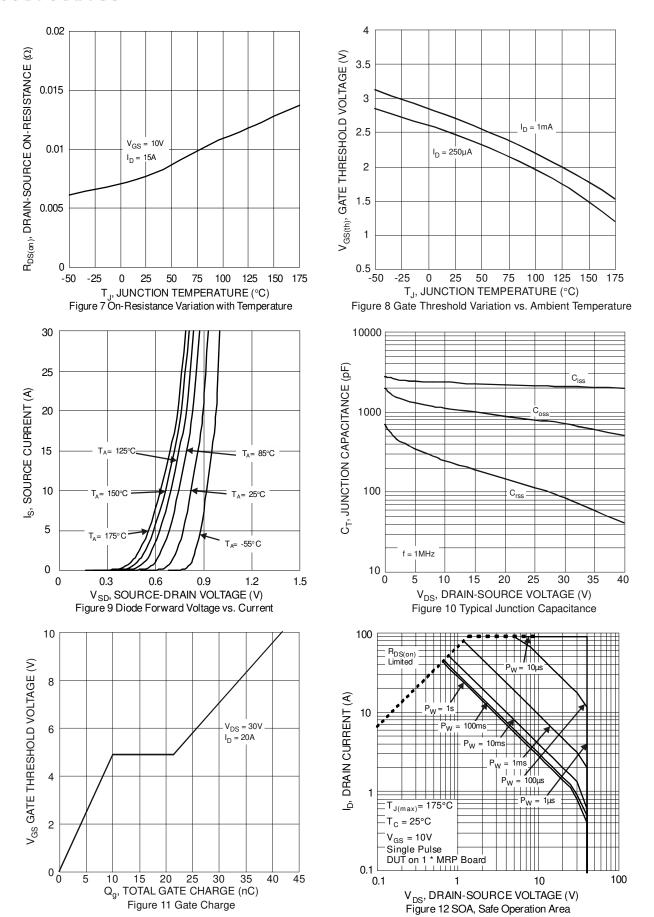
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	_	1	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(TH)}$	2	_	4	V	$V_{DS}=V_{GS},\ I_D=250\mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	7.5	8.6	mΩ	$V_{GS} = 10V, I_D = 17A$	
Diode Forward Voltage	$V_{SD}$	_	0.85	_	V	$V_{GS} = 0V, I_S = 17A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	CISS	_	2,026		pF	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	_	702	_	pF		
Reverse Transfer Capacitance	C <sub>RSS</sub>	_	84.8	_	pF		
Gate Resistance	Rg	_	0.46		Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Q <sub>G</sub>	_	41.9		nC		
Gate-Source Charge	Q <sub>GS</sub>	_	10	_	nC	$V_{DS} = 30V$ , $I_D = 20A$ , $V_{GS} = 10V$	
Gate-Drain Charge	$Q_{GD}$	_	11.5	_	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	7	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	11.5	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	15.6	_	ns	$I_D = 20A$ , $R_G = 3\Omega$	
Turn-Off Fall Time	t <sub>F</sub>	_	8.8	_	ns		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	29.9	_	ns	I_ 20.0 di/dt 100.0 /u.c	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	23	_	nC		

Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.
 Package limited.

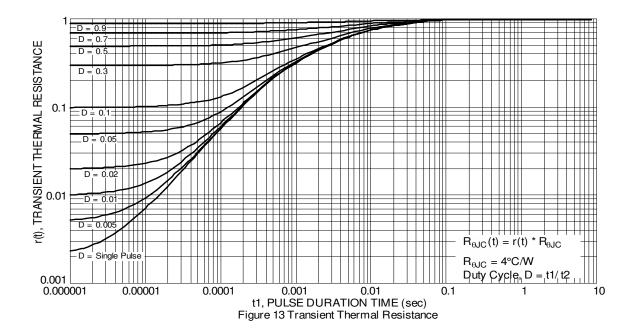










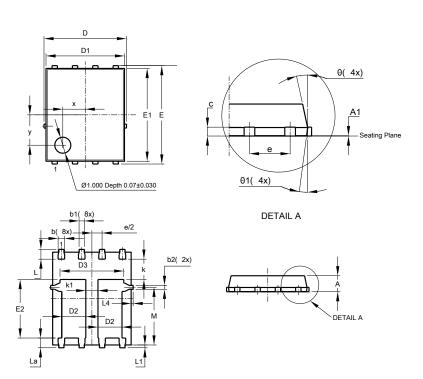




## **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

### PowerDI5060-8 (Type C)

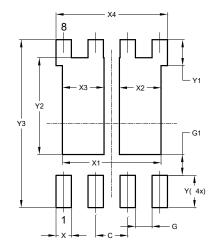


PowerDI5060-8 (Type C)					
Dim	Min	Тур			
Α	0.90	1.10	1.00		
<b>A</b> 1	0	0.05	0.02		
b	0.33	0.51	0.41		
b1	0.300	0.366	0.333		
b2	0.20	0.35	0.25		
С	0.23	0.33	0.277		
D	5	.15 BS0	2		
D1	4.85	4.95	4.90		
D2	1.40	1.60	1.50		
D3	1	-	3.98		
Е	6	.15 BS0	2		
E1	5.75	5.85	5.80		
E2	3.56	3.76	3.66		
е	1	.27BS0			
k	-	-	1.27		
k1	0.56	-	-		
L	0.51	0.71	0.61		
La	0.51	0.71	0.61		
L1	0.05	0.20	0.175		
L4	-	-	0.125		
М	3.50	3.71	3.605		
Х			1.400		
у	-	-	1.900		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

#### PowerDI5060-8 (Type C)



Dimensions	Value			
Dimensions	(in mm)			
С	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	3.910			
X2	1.650			
Х3	1.650			
X4	4.420			
Υ	1.270			
<b>Y</b> 1	1.020			
Y2	3.810			
Y3	6.610			



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